# Single Buffer, Non-Inverting, TTL Level

# **TTL-Compatible Inputs**

The NLU1GT50 MiniGate<sup>™</sup> is an advanced CMOS high-speed non-inverting buffer in ultra-small footprint.

The device input is compatible with TTL-type input thresholds and the output has a full 5.0 V CMOS level output swing.

The NLU1GT50 input and output structures provide protection when voltages up to 7.0 V are applied, regardless of the supply voltage.

### **Features**

- Designed for 1.65 to 5.5 V V<sub>CC</sub> Operation
- High Speed:  $t_{PD} = 3.5 \text{ ns (Typ)} @ V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 1 \mu A$  (Max) at  $T_A = 25^{\circ}C$
- TTL-Compatible Input:  $V_{IL} = 0.8 \text{ V}$ ;  $V_{IH} = 2.0 \text{ V}$ ,  $V_{CC} = 5.0 \text{ V}$
- CMOS-Compatible Output:
  - $V_{OH} > 0.8 V_{CC}$ ;  $V_{OL} < 0.1 V_{CC}$  @ Load
- Power Down Protection Provided on inputs
- Balanced Propagation Delays
- Ultra-Small Packages
- These are Pb-Free Devices

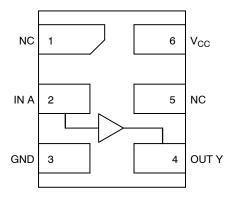


Figure 1. Pinout (Top View)

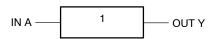


Figure 2. Logic Symbol

<b>FUNCTION TABLE</b>					
Α	Y				

L

1	NC
2	IN A
3	GND
4	OUT Y
5	NC
6	V <sub>CC</sub>

**PIN ASSIGNMENT** 



# ON Semiconductor®

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# MARKING DIAGRAMS



UDFN6 MU SUFFIX CASE 517AA





ULLGA6 1.0 x 1.0 CASE 613AD





ULLGA6 1.45 x 1.0 CASE 613AF





UDFN6 1.0 x 1.0 CASE 517BX





UDFN6 1.45 x 1.0 CASE 517AQ



L = Device Marking
M = Date Code

### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 4 of this data sheet.

### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage	-0.5 to +7.0	V
V <sub>IN</sub>	DC Input Voltage	-0.5 to +7.0	V
V <sub>OUT</sub>	DC Output Voltage	-0.5 to +7.0	V
I <sub>IK</sub>	DC Input Diode Current V <sub>IN</sub> < GND	-20	mA
lok	DC Output Diode Current V <sub>OUT</sub> < GND	±20	mA
I <sub>O</sub>	DC Output Source/Sink Current	±12.5	mA
I <sub>CC</sub>	DC Supply Current Per Supply Pin	±25	mA
I <sub>GND</sub>	DC Ground Current per Ground Pin	±25	mA
T <sub>STG</sub>	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C
TJ	Junction Temperature Under Bias	150	°C
MSL	Moisture Sensitivity	Level 1	
F <sub>R</sub>	Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V <sub>ESD</sub>	ESD Withstand Voltage  Human Body Model (Note 2)  Machine Model (Note 3)  Charged Device Model (Note 4)	> 2000 > 200 N/A	٧
I <sub>LATCHUP1</sub>	Latchup Performance Above V <sub>CC</sub> and Below GND at 125 °C (Note 5)	±500	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow.

- 2. Tested to EIA / JESD22-A114-A.
- 3. Tested to EIA / JESD22-A115-A.
- 4. Tested to JESD22-C101-A.
- 5. Tested to EIA / JESD78.

# **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	Positive DC Supply Voltage	1.65	5.5	٧
V <sub>IN</sub>	Digital Input Voltage	0	5.5	٧
V <sub>OUT</sub>	Output Voltage	0	5.5	٧
T <sub>A</sub>	Operating Free-Air Temperature	-55	+125	°C
Δt/ΔV	Input Transition Rise or Fall Rate $ V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}  $ $ V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}  $	0 0	100 20	ns/V

# DC ELECTRICAL CHARACTERISTICS

				т,	T <sub>A</sub> = 25 °C		= 25 °C		T <sub>A</sub> = -55°C to +125°C		
Symbol	Parameter	Conditions	V <sub>CC</sub> (V)	Min	Тур	Max	Min	Max	Min	Max	Unit
$V_{IH}$	Low-Level Input Voltage		1.65 to 2.29	0.50 x V <sub>CC</sub>			0.50 x V <sub>CC</sub>				V
	voltage		2.3 to 2.99	0.45 x V <sub>CC</sub>			0.45 x V <sub>CC</sub>				
			3.0	1.4			1.4				
			4.5 to 5.5	2.0			2.0				
V <sub>IL</sub>	Low-Level Input Voltage		1.65 to 2.29			0.10 x V <sub>CC</sub>		0.10 x V <sub>CC</sub>		0.10 x V <sub>CC</sub>	٧
	voltago		2.3 to 2.99			0.15 x V <sub>CC</sub>		0.15 x V <sub>CC</sub>		0.15 x V <sub>CC</sub>	
			3.0			0.53		0.53		0.53	
			4.5 to 5.5			0.8		0.8		0.8	
V <sub>OH</sub>	OH High-Level Output Voltage	$V_{IN} = V_{IH}$ or $V_{IL}$	1.65 to 2.99	V <sub>CC</sub> - 0.1			V <sub>CC</sub> - 0.1		V <sub>CC</sub> - 0.1		٧
		I <sub>OH</sub> = -50 μA	3.0	2.9	3.0		2.9		2.9		
			4.5	4.4	4.5		4.4		4.4		
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V <sub>OL</sub>	Low-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$	1.65 to 2.99		0	0.1		0.1		0.1	٧
	voltage		3.0		0	0.1		0.1		0.1	
			4.5		0	0.1		0.1		0.1	
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4 \text{ mA}$ $I_{OL} = 8 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I <sub>IN</sub>	Input Leakage Current	0 = V <sub>IN</sub> = 5.5 V	0 to 5.5			±0.1		±1.0		±1.0	μΑ
I <sub>CC</sub>	Quiescent Supply Current	V <sub>IN</sub> = 5.5 V or GND	5.5			1.0		20		40	μΑ
I <sub>CCT</sub>	Quiescent Supply Current	V <sub>IN</sub> = 3.4 V	5.5			1.35		1.50		1.65	mA
I <sub>OPD</sub>	Output Leakage Current	V <sub>OUT</sub> = 5.5 V	0.0			0.5		5.0		10	μΑ

# AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ n}$ )

			Test	T <sub>A</sub> = 25 °C		T <sub>A</sub> = 25 °C		T <sub>A</sub> = -55°C to +125°C			
Symbol	Parameter	V <sub>CC</sub> (V)	Condition	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> ,	Propagation Delay, Input A to Output ₹	1.65 to 1.95	C <sub>L</sub> = 15 pF			16.6		18.0		22.0	ns
t <sub>PHL</sub>	input A to Output Y	2.3 to 2.7	C <sub>L</sub> = 15 pF			13.3		14.5		17.5	
			C <sub>L</sub> = 50 pF			19.5		22.0		25.5	
		3.0 to 3.6	C <sub>L</sub> = 15 pF		4.5	10.0		11.0		13.0	
			C <sub>L</sub> = 50 pF		6.3	13.5		15.0		17.5	
		4.5 to 5.5	C <sub>L</sub> = 15 pF		3.5	6.7		7.5		8.5	
			C <sub>L</sub> = 50 pF		4.3	7.7		8.5		9.5	
C <sub>IN</sub>	Input Capacitance				5	10		10		10.0	pF
C <sub>PD</sub>	Power Dissipation Capacitance (Note 6)	5.0			12						pF

<sup>6.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the dynamic operating current consumption without load. Average operating current can be obtained by the equation I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>. C<sub>PD</sub> is used to determine the no–load dynamic power consumption: P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

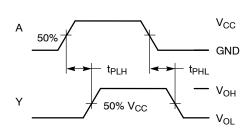
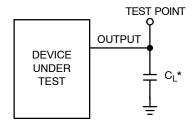


Figure 3. Switching Waveforms



\*Includes all probe and jig capacitance

Figure 4. Test Circuit

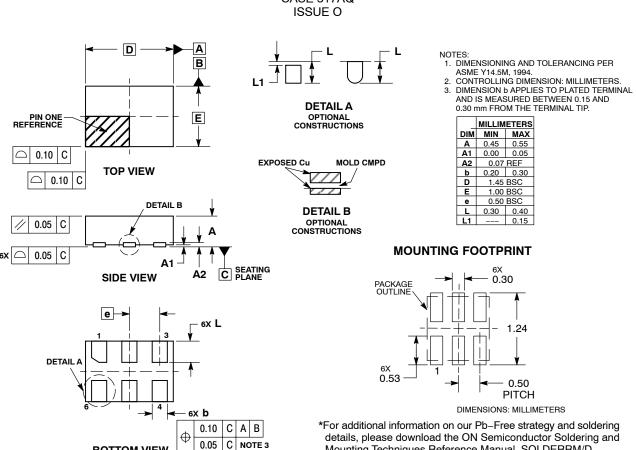
### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NLU1GT50MUTCG	UDFN6, 1.2 x 1.0, 0.4P (Pb-Free)	3000 / Tape & Reel
NLU1GT50AMX1TCG	ULLGA6, 1.45 x 1.0, 0.5P (Pb-Free)	3000 / Tape & Reel
NLU1GT50CMX1TCG	ULLGA6, 1.0 x 1.0, 0.35P (Pb-Free)	3000 / Tape & Reel
NLU1GT50AMUTCG	UDFN6, 1.45 x 1.0, 0.5P (Pb-Free)	3000 / Tape & Reel
NLU1GT50CMUTCG	UDFN6, 1.0 x 1.0, 0.35P (Pb-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### **PACKAGE DIMENSIONS**

# UDFN6 1.45x1.0, 0.5P CASE 517AQ

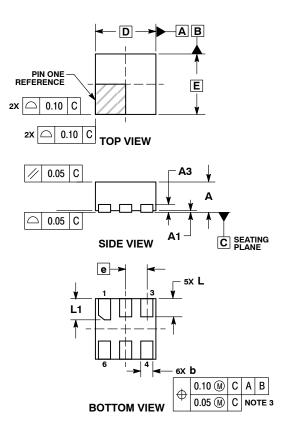


Mounting Techniques Reference Manual, SOLDERRM/D.

**BOTTOM VIEW** 

### **PACKAGE DIMENSIONS**

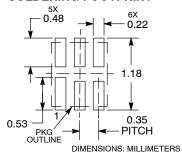
UDFN6 1.0x1.0, 0.35P CASE 517BX ISSUE O



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
   CONTROLLING DIMENSION: MILLIMETERS.
   DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.
   PACKAGE DIMENSIONS EXCLUSIVE OF DIMENSIONS EXCLUSIVE OF
- BURRS AND MOLD FLASH.

	MILLIMETERS				
DIM	MIN	MAX			
Α	0.45	0.55			
A1	0.00	0.05			
А3	0.13 REF				
b	0.12	0.22			
D	1.00 BSC				
E	1.00 BSC				
е	0.35 BSC				
L	0.25	0.35			
L1	0.30	0.40			

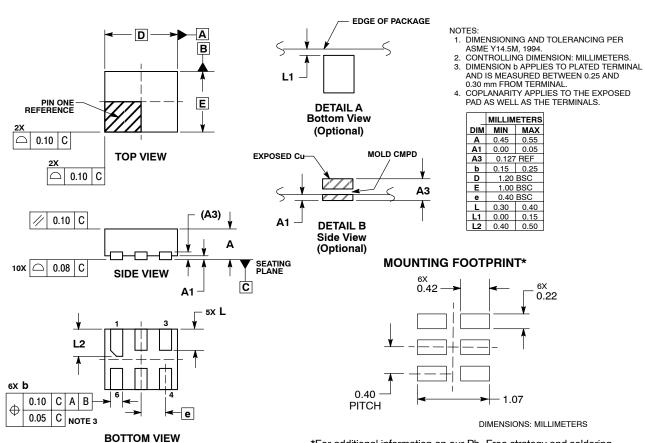
### **RECOMMENDED SOLDERING FOOTPRINT\***



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# **PACKAGE DIMENSIONS**

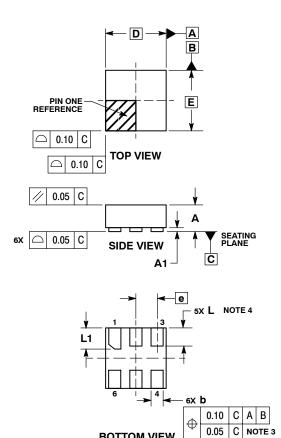
### UDFN6, 1.2x1.0, 0.4P CASE 517AA ISSUE D



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### **PACKAGE DIMENSIONS**

### ULLGA6 1.0x1.0, 0.35P CASE 613AD **ISSUE A**



**BOTTOM VIEW** 

### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

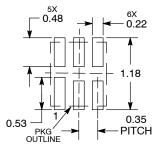
  2. CONTROLLING DIMENSION: MILLIMETERS.

  3. DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM THE TERMINAL TIP.

  4. A MAXIMUM OF 0.05 PULL BACK OF THE PLATED TERMINAL FROM THE EDGE OF THE PACKAGE IS ALLOWED.

	MILLIMETERS				
DIM	MIN	MAX			
Α		0.40			
A1	0.00	0.05			
b	0.12	0.22			
D	1.00	BSC			
E	1.00 BSC				
е	0.35 BSC				
L	0.25	0.35			
11	0.30	0.40			

### **MOUNTING FOOTPRINT SOLDERMASK DEFINED\***

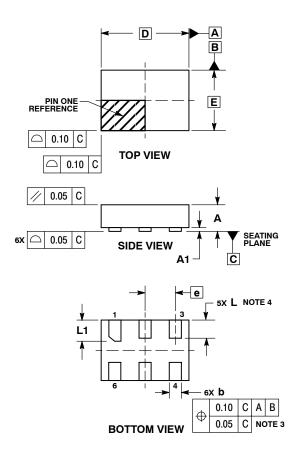


DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### PACKAGE DIMENSIONS

### ULLGA6 1.45x1.0, 0.5P CASE 613AF ISSUE A

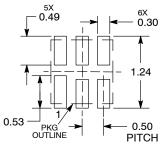


### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.
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- A MAXIMUM OF 0.05 PULL BACK OF THE PLATED TERMINAL FROM THE EDGE OF THE PACKAGE IS ALLOWED.

	<b>MILLIMETERS</b>				
DIM	MIN	MAX			
Α		0.40			
A1	0.00	0.05			
b	0.15	0.25			
D	1.45 BSC				
E	1.00 BSC				
е	0.50 BSC				
L	0.25	0.35			
L1	0.30	0.40			

### MOUNTING FOOTPRINT SOLDERMASK DEFINED\*



DIMENSIONS: MILLIMETERS

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